



21st International Liquid Crystal Conference

Keystone, Colorado July 2 - 7, 2006

PROGRAM SUPPLEMENT

Organized by:



The Liquid Crystal Materials Research Center University of Colorado, Boulder

Tuesday, July 4

Poster Session 5, 3:30 PM - 4:30 PM

Posters - Devices and applications DEVIP Quandary Room: DEVIP-4 CHANGED TO ORAL CONTRIBUTION DEVI1-03 Microwave variable phase shifter of microstrip and coplanar waveguide structures using ferroelectric liquid crystal H. Moritake, S. Morita, R. Ozaki, T. Kamei, Y. Utsumi National Defense Academy, Japan **DEVIP-18** CHANGED TO DIFFERENT POSTER SESSION SYNTP-92 All aromatic, nonlinear mesogens with heterocyclic units N. A. Zafiropoulos, T. J. Dingemans, E. J. Choi, W. Lin, E. T. Samulski University of North Carolina at Chapel Hill, USA Electrically-switchable, polarization-independent diffraction grating based on negative **DEVIP-80** dielectric anisotropy liquid crystal M. H. Zhu, G. Carbone, and C. Rosenblatt Case Western Reserve University, USA The effect of interfacial roughness on the electrical properties of organic thin film DEVIP-81 transistors with an anisotropic dielectric layer J. I. Jung, H. R. Kim, J. Y. Song, and J. H. Kim Hanyang Univesity, South Korea Novel Patterned Vertical Alignment LCD for Mobile Application with High Transmittance DEVIP-82 and Reliability J. H. Kim, Y. S. Yeo, W. S. Park, S. K. Lee, S. H. Ahn, and C. W. Kim Samsung Electronics Co., Ltd., South Korea DEVIP-83 Prove of biaxial nematic phase by electro-optical properties C. Shin, N. C. Choi, D. W. Kim, H. Choi, W. T. Kim, J. I. Jin, and S. T. Shin Korea University, South Korea DEVIP-84 Multi-reflection effects in the black state of a LCD P. J. Bos, and Y. K. Jang Kent State University, USA Rotating polarizing technique for the determination of phase transitions of liquid crystals DEVIP-85 L. Somayajula Acharva Nagariuna University, India Computational studies of liquid crystal non-linear optics DEVIP-86 V. I. Hazelwood, T. J. Sluckin, S. L. Subota, S. J. Cox University of Southampton, United Kingdom

DEVIP-81

The effect of interfacial roughness on the electrical properties of organic thin film transistors with an anisotropic dielectric layer

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Organic thin film transistors (OTFTs) have drawn much attention for flexible electronics such as smart cards, flexible displays, and several types of low cost and low-end electronics. Recently, OTFTs with fold-effect mobility and on/off ratio current ratio comparable to a-Si:H thin film transistors have been fabricated. Since the electrical conduction of OTFTs is highly affected by the molecular ordering, crystalline orientation, and the crystallized grain size of the organic semiconductors, there were several efforts to modify interfacial properties between the evaporated pentacene molecules and the insulator surface. In general, highly oriented polymeric layers by mechanical rubbing or irradiation of polarized UV light were used for the purpose. But, the electrical performances of OTFTs on the organic insulators are not satisfactory yet, comparing with those on the inorganic insulators, especially in terms of leakage current, the driving gate voltage, and stability in ambient condition. In this paper, we investigated anisotropic conduction effects of pentacene-based OTFT on an anisotropic insulator fabricated by obliquely evaporated silicon dioxide. As the evaporation angle of SiO2 increased, the anisotropic interaction at the dielectric interface and molecular ordering of evaporated pentacenes increased. However, in highly obliquely evaporated dielectric surface, it was observed that growth of the pentacene molecules was highly limited due to increased roughness at the interace. The molecular ordering effect and the grain size effect depending on the surface anisotropy and the surface roughness were discussed with the results of the field-induced mobility and the surface morphology. We believe that further optimization of oblique evaporation in OTFTs would result in more anisotropic electrical property.